



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92S Plastic-Encapsulate Transistors

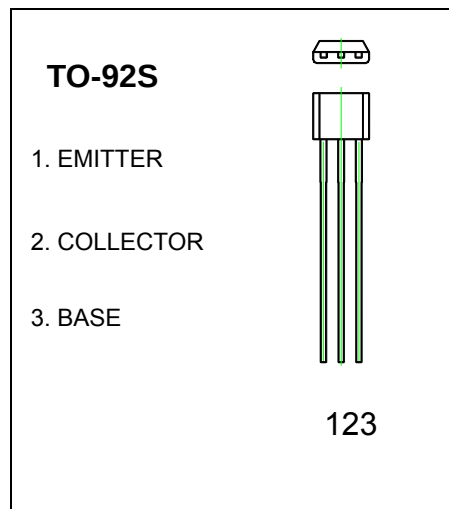
2SD1468S TRANSISTOR (NPN)

FEATURES

- Low saturation voltage, typically $V_{ce(sat)}=0.006V$
- Ideal for voltage, high current drives,
- High DC current gain and high current

MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	15	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1	A
P_C	Collector Power Dissipation	300	mW
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu A, I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	15			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=20V, I_E=0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			0.5	μA
DC current gain	h_{FE}	$V_{CE}=3V, I_C=100mA$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			0.4	V
Transition frequency	f_T	$V_{CE}=5V, I_C=50mA, f=100MHz$	50			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$			30	pF

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120-270	180-390	270-560

Typical Characteristics

2SD1468S

